

A SEMICONDUCTOR ACCELEROMETER

Abstract of the Invention

5 A movable gate metal oxide field effect transistor (MOSFET) (1) includes a movable gate (4) and a plate (30). The movable gate (4) and the plate (30) are coupled to a direct current (DC) voltage source (35) to apply a voltage V. The voltage V from the direct current (DC) voltage source (35) causes an electrostatic force between the plate (30) and the gate (4), and
10 enables the position of the movable gate (4) to be controlled to significantly reduce the sensitivity of the movable gate MOSFET (1) to changes other than those caused by an accelerative or decelerative force.

(FIG. 3 accompanies this abstract)